

DOCKET NO. 99-039

#13/c
3/29/03



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Sheldon Aronowitz, Valeriy Sukharev, John Haywood, James P. Kimball, Helmut Puchner, Ravindra Manohar Kapre, and Nicholas Eib

Appl. No. : 09/464,297

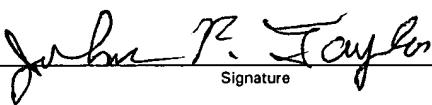
Filed: December 15, 1999

Title : PROCESS FOR ETCHING A CONTROLLABLE THICKNESS OF OXIDE ON AN INTEGRATED CIRCUIT STRUCTURE ON A SEMICONDUCTOR SUBSTRATE USING NITROGEN PLASMA AND AN RF BIAS APPLIED TO THE SUBSTRATE

Grp./ A.U. : 1765

Examiner : Charlotte A. Brown

Docket No. : 99-039

CERTIFICATE OF MAILING	
I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231	
on	<u>March 20, 2003</u>
(Date of Deposit)	
John P. Taylor, Reg. No. 22,369	
 _____ Signature	
<u>March 20, 2003</u>	
_____ Date of Signature	

AMENDMENT

Honorable Commissioner for Patents
Washington, D.C. 20231

RECEIVED
U.S. MAIL ROOM
MAR 27 2003
Date: March 20, 2003

Sir:

In response to the Office Action mailed January 7, 2003, please amend the application as follows: